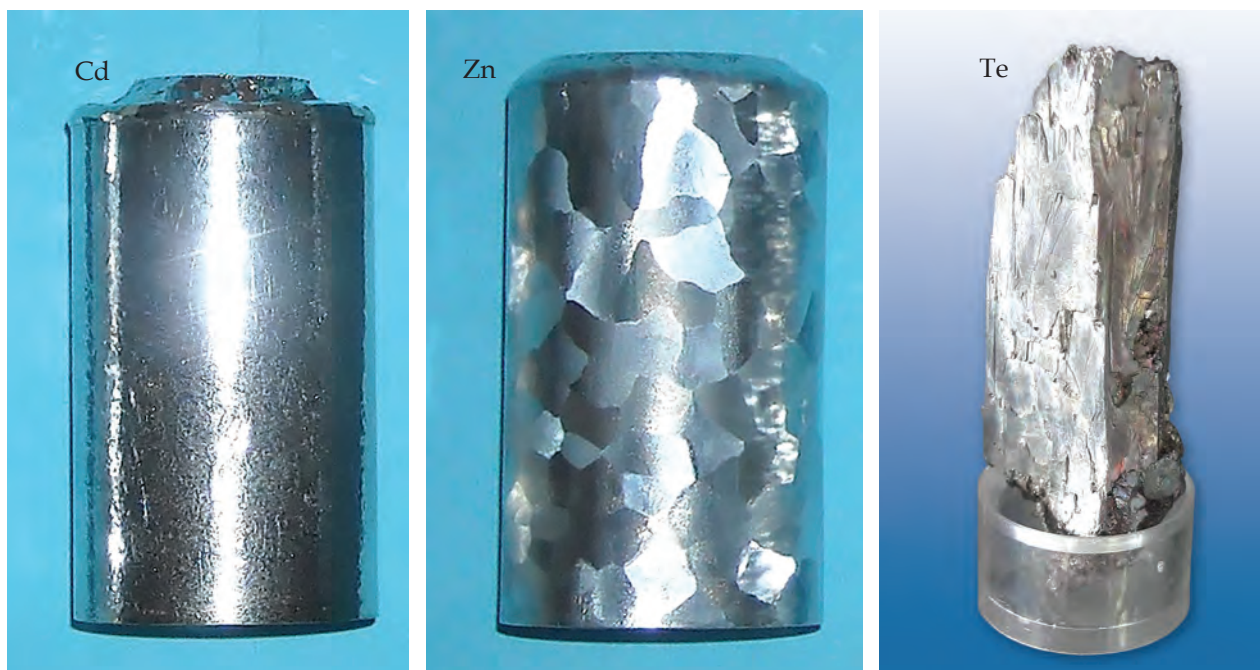


DEVICE FOR DEEP PURIFICATION OF Cd, Zn, AND Te



Areas of Application

The device is designed for obtaining semiconductor and scintillation crystals for ionizing radiation detectors

Specification

Weight of original charge, kg	2.5
Product yield, % of original charge	90
Yield capacity, g/hour	300 – 400
Power capacity, kW	≤3
Operating temperature, °C	350 – 650
Fineness, %	99.9 – 99.99... >99.999 – 99.9999

Advantages

The equipment is unique in Ukraine.  
Deep purification from a wide range of impurities;  
high efficiency of the refining process;  
high product yield

IPR Protection

IPR3

Stage of Development.

Suggestions for Commercialization

IRL6, TRL6  
Pure metals manufactured, upon request

Contact Information

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